

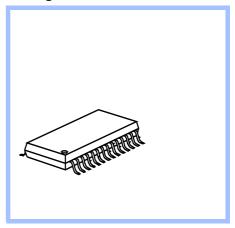
Product Info

Product Info

General Description

The IC is a very low power consumption single chip FSK/ASK Superheterodyne Receiver (SHR) for the receive frequency range between 910 and 920 MHz that is pin compatible to the ASK Receiver TDA5202. The IC offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a PLL FSK demodulator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

Package



Features

Low supply current ($I_s = 5.4 \text{ mA typ.}$ in FSK mode, $I_s = 4.8 \text{ mA typ.}$ in ASK mode)

Supply voltage range 5 V ±10%

Power down mode with very low supply current (90 nA typ.)

FSK and ASK demodulation capability

Fully integrated VCO and PLL Synthesiser

ASK sensitivity better than -109 dBm over specified temperature range (- 40 to +85°C) Receive frequency range 910 to 920 MHz

Limiter with RSSI generation, operating at 10.7 MHz

Selectable reference frequency

2nd order low pass data filter with external capacitors

Data slicer with self-adjusting threshold

FSK sensitivity better than -102 dBm over specified temperature range (- 40 to +85°C)

Application

Keyless Entry Systems Remote Control Systems Low Bitrate ISM-band Communication Systems

Ordering Information

Туре	Ordering Code	Package
TDA 5212		P-TSSOP-28-1
samples available		

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Product Description

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Product Description



2.1 Overview

The IC is a very low power consumption single chip FSK/ASK Superheterodyne Receiver (SHR) for receive frequencies between 910 and 920 MHz that is pin compatible to the ASK Receiver TDA5202. The IC offers a high level of integration and needs only a few external components. The device contains a low noise amplifier (LNA), a double balanced mixer, a fully integrated VCO, a PLL synthesiser, a crystal oscillator, a limiter with RSSI generator, a PLL FSK demodulator, a data filter, a data comparator (slicer) and a peak detector. Additionally there is a power down feature to save battery life.

2.2 Application

Keyless Entry Systems
Remote Control Systems

Low Bitrate ISM-band Communication Systems

2.3 Features

Low supply current ($I_s = 5.4 \text{ mA typ.FSK mode}$, 4.8 mA typ. ASK mode)

Supply voltage range 5V ±10%

Power down mode with very low supply current (90nA typ.)

FSK and ASK demodulation capability

Fully integrated VCO and PLL Synthesiser

RF input sensitivity ASK -112dBm typ. at 25°C, better than -109dBm over complete specified operating temperature range (-40 to +85°C)

RF input sensitivity FSK -105dBm typ. at 25°C, better than -102dBm over complete specified operating temperature range (-40 to +85°C)

Receive frequency range between 910 and 920 MHz

Selectable reference frequency

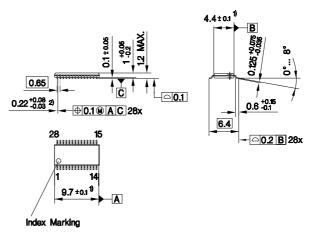
Limiter with RSSI generation, operating at 10.7MHz

2nd order low pass data filter with external capacitors

Data slicer with self-adjusting threshold

Product Description

2.4 Package Outlines



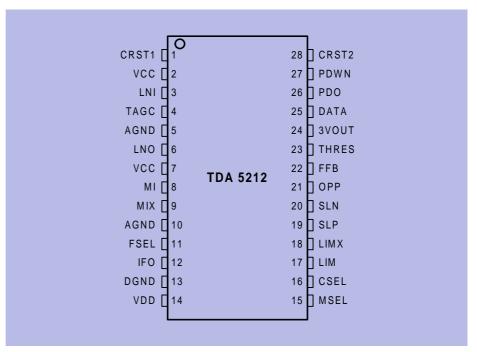
- 1) Does not include plastic or metal protrusion of 0.15 max. per side
- 2) Does not include dambar protrusion

P_TSSOP_28.EPS

Figure 2-1 P-TSSOP-28-1 package outlines

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3.1 Pin Configuration



Pin_Configuration_5212_V1.0.wmf

Figure 3-1 IC Pin Configuration



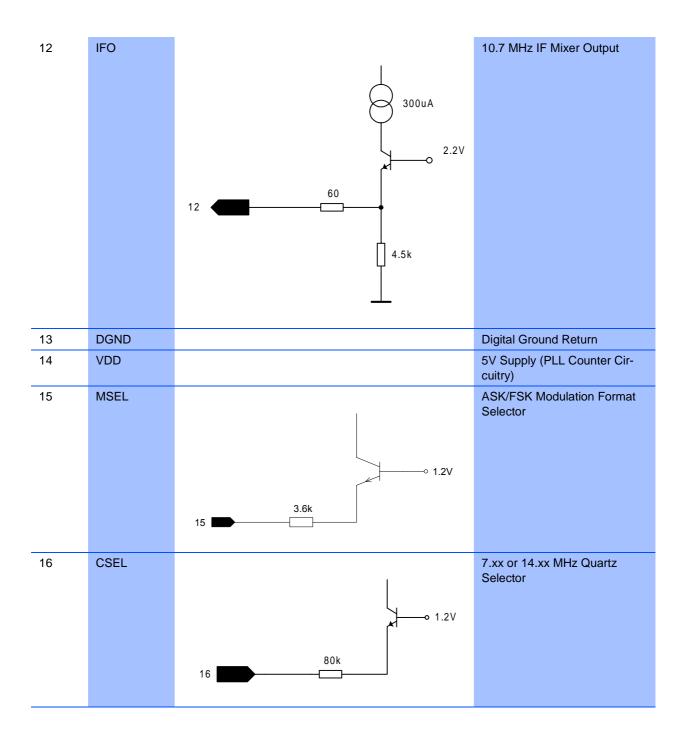
3.2 Pin Definition and Function

Table 3-1	Pin Definition	and Function	
Pin No.	Symbol	Equivalent I/O-Schematic	Function
1	CRST1	4.15V 50uA	External Crystal Connector 1
2	VCC		5V Supply
3	LNI	57uA 3 500uA	LNA Input

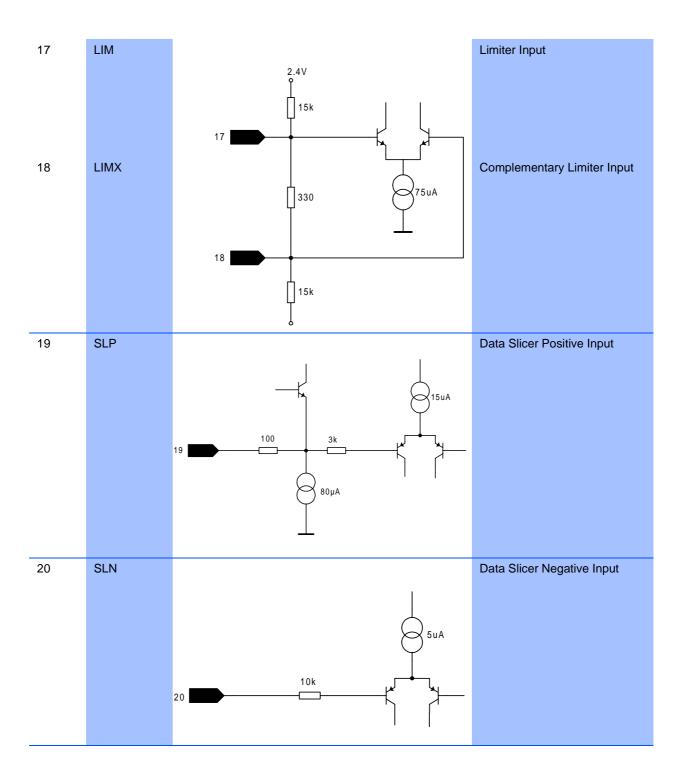


4	TAGC		AGC Time Constant Control
		4.3V	
		3u A	
		_41k	
		1.4uA	
		 1.7V	
	AGND	1.77	Analogue Cround Poturn
5 6	LNO		Analogue Ground Return LNA Output
O	LINO	5V	LIVA Output
		1	
		Y	
		6	
		Ļ	
		h	
7	VCC		5V Supply
8	MI		Mixer Input
		1.7V Ŷ	
		2k 2k	
9	MIX		Complementary Mixer Input
		9	
		400uA	
			
10	AGND		Analogue Ground Return
11	BUF		Mixer Buffer Ground

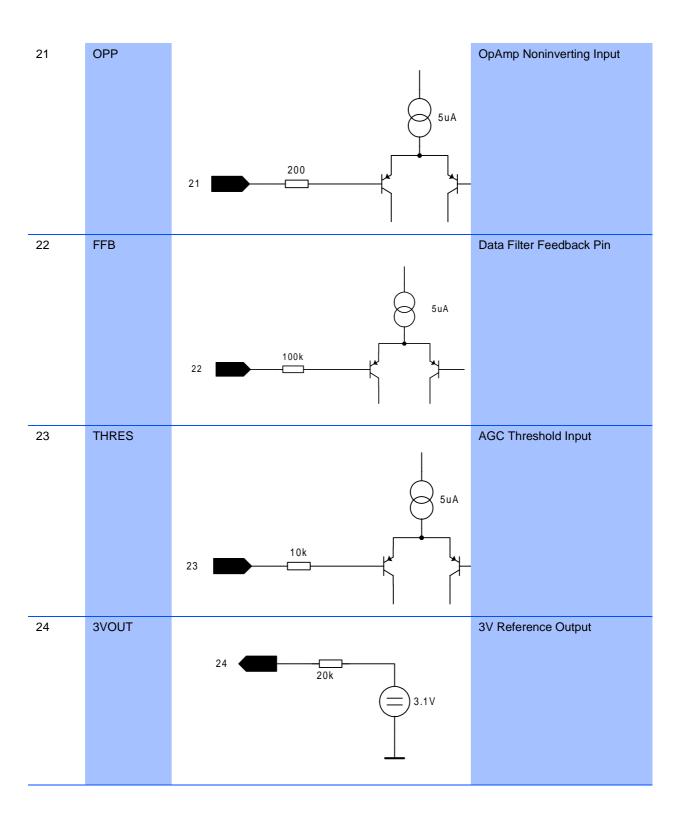














25	DATA	25 ————————————————————————————————————	Data Output
26	PDO	26	Peak Detector Output
27	PDWN	220k	Power Down Input
28	CRST2	4.15V 50uA	External Crystal Connector 2



3.3 Functional Block Diagram

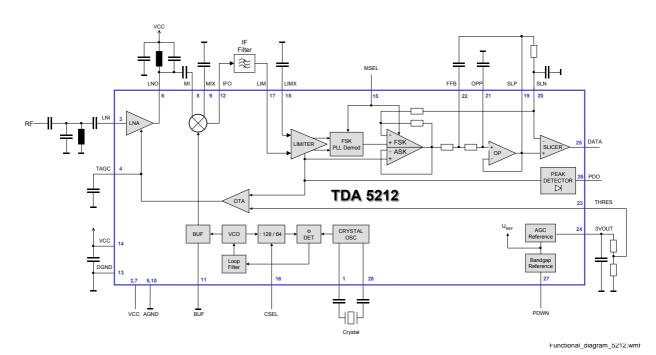


Figure 3-2 Main Block Diagram



3.4 Functional Blocks

3.4.1 Low Noise Amplifier (LNA)

The LNA is an on-chip cascode amplifier with a voltage gain of 15 to 20dB. The gain figure is determined by the external matching networks situated ahead of LNA and between the LNA output LNO (Pin 6) and the Mixer Inputs MI and MIX (Pins 8 and 9). The noise figure of the LNA is approximately 2dB, the current consumption is 500µA. The gain can be reduced by approximately 18dB. The switching point of this AGC action can be determined externally by applying a threshold voltage at the THRES pin (Pin 23). This voltage is compared internally with the received signal (RSSI) level generated by the limiter circuitry. In case that the RSSI level is higher than the threshold voltage the LNA gain is reduced and vice versa. The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin as described in Section 4.1. The time constant of the AGC action can be determined by connecting a capacitor to the TAGC pin (Pin 4) and should be chosen along with the appropriate threshold voltage according to the intended operating case and interference scenario to be expected during operation. The optimum choice of AGC time constant and the threshold voltage is described in Section 4.1.

3.4.2 Mixer

The Double Balanced Mixer downconverts the input frequency (RF) in the range of 910 to 920 MHz to the intermediate frequency (IF) at 10.7MHz with a voltage gain of approximately 21dB. A low pass filter with a corner frequency of 20MHz is built on chip in order to suppress RF signals to appear at the IF output (**IFO** pin). The IF output is internally consisting of an emitter follower that has a source impedance of approximately 330 Ω to facilitate interfacing the pin directly to a standard 10.7MHz ceramic filter without additional matching circuitry.

3.4.3 PLL Synthesizer

The Phase Locked Loop synthesiser consists of a VCO, an asynchronous divider chain, a phase detector with charge pump and a loop filter and is fully implemented on-chip. The VCO is including spiral inductors and varactor diodes. The oscillator signal is fed both to the synthesiser divider chain and to the downconverting mixer via a buffer amplifier. The **BUF** pin (Pin 11) has to be tied to ground. No additional components are necessary. The loop filter is also realised fully on-chip. High-side injection of the local oscillator has to be used for the receive frequency band of 910 to 920 MHz, yielding local oscillator frequencies in the region of 920 to 930 MHz. See also Section 4.4.



3.4.4 Crystal Oscillator

The on-chip crystal oscillator circuitry allows for utilisation of quartzes both in the 7 and 14MHz range as the overall division ratio of the PLL can be switched between 64 and 128 via the **CSEL** (Pin 16) pin according to the following table.

Table 3-2 CSEL Pin Operating States	
CSEL	Crystal Frequency
Open	7.xx MHz
Shorted to ground	14.xx MHz

The calculation of the value of the necessary quartz load capacitance is shown in Section 4.3, the quartz frequency calculation is expained in Section 4.4.

3.4.5 Limiter

The Limiter is an AC coupled multistage amplifier with a cumulative gain of approximately 80dB that has a bandpass-characteristic centred around 10.7MHz. It has an input impedance of 330 Ω to allow for easy interfacing to a 10.7MHz ceramic IF filter. The limiter circuit acts as a Receive Signal Strength Indicator (RSSI) generator which produces a DC voltage that is directly proportional to the input signal level as can be seen in Figure 4-2. This signal is used to demodulate the ASK receive signal in the subsequent baseband circuitry and to turn down the LNA gain by approximately 18dB in case the input signal strength is too strong as described in Section 3.4.1 and Section 4.1.

3.4.6 FSK Demodulator

To demodulate frequency shift keyed (FSK) signals a PLL circuit is used that is contained fully on chip. The Limiter output differential signal is fed to the linear phase detector as is the output of the 10.7 MHz center frequency VCO. The demodulator gain is typically $180\mu\text{V/kHz}$. The passive loop filter output that is comprised fully on chip is fed to both the VCO and the modulation format switch. This signal is representing the demodulated signal. This switch is actually a switchable amplifier with an AC gain of 11 that is controlled by the **MSEL** pin (Pin 15) as shown in the following table. This gain was chosen to facilitate detection in the subsequent circuits.

Table 3-3 MSEL Pin Operating States	
MSEL	Modulation Format
Open	ASK
Shorted to ground	FSK



The DC gain is 1 in order not to saturate the subsequent Data Filter wih the DC offset produced by the demodulator in case of large frequency offsets of the IF signal. The resulting frequency characteristic and details on the principle of operation of the switch are described in Section 4.6. The demodulator circuit is switched off in case of reception of ASK signals.

3.4.7 Data Filter

The data filter comprises an OP-Amp with a bandwidth of 100kHz used as a voltage follower and two $100k\Omega$ on-chip resistors. Along with two external capacitors a 2nd order Sallen-Key low pass filter is formed. The selection of the capacitor values is described in Section 4.2.

3.4.8 Data Slicer

The data slicer is a fast comparator with a bandwidth of 100 kHz. This allows for a maximum receive data rate of approximately 120kBaud. The maximum achievable data rate also depends on the IF Filter bandwidth and the local oscillator tolerance values. Both inputs are accessible. The output delivers a digital data signal (CMOS-like levels) for the detector. The self-adjusting threshold on pin 20 its generated by RC-term or peak detector depending on the baseband coding scheme. The data slicer threshold generation alternatives are described in more detail in Section 4.5.

3.4.9 Peak Detector

The peak detector generates a DC voltage which is proportional to the peak value of the receive data signal. An external RC network is necessary. The input is connected to the output of the RSSI-output of the Limiter, the output is connected to the PDO pin (Pin 26). This output can be used as an indicator for the received signal strength to use in wake-up circuits and as a reference for the data slicer in ASK mode. The output current is typically $850\mu\text{A}$, the leakage current is typically 700nA. Note that the RSSI level is also output in case of FSK mode.



3.4.10 Bandgap Reference Circuitry

A Bandgap Reference Circuit provides a temperature stable reference voltage for the device. A power down mode is available to switch off all subcircuits which is controlled by the **PWDN** pin (Pin 27) as shown in the following table. The supply current drawn in this case is typically 90nA.

Table 3-4 PDWN Pin Operating States		
PDWN	Operating State	
Open or tied to ground	Powerdown Mode	
Tied to Vs	Receiver On	

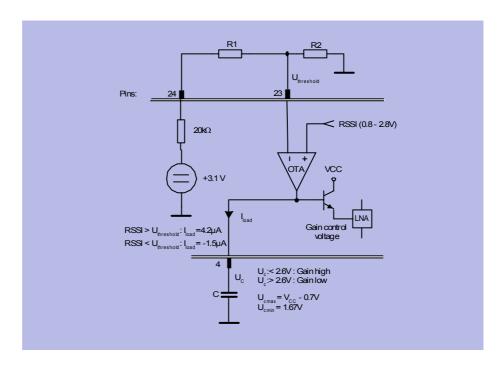
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4.1 Choice of LNA Threshold Voltage and Time Constant

In the following figure the internal circuitry of the LNA automatic gain control is shown.



LNA_autom.wmf

Figure 4-1 LNA Automatic Gain Control Circuitry

The LNA automatic gain control circuitry consists of an operational transimpedance amplifier that is used to compare the received signal strength signal (RSSI) generated by the Limiter with an externally provided threshold voltage U_{thres} . As shown in the following figure the threshold voltage can have any value between approximately 0.8 and 2.8V to provide a switching point within the receive signal dynamic range.

This voltage U_{thres} is applied to the **THRES** pin (Pin 23) The threshold voltage can be generated by attaching a voltage divider between the **3VOUT** pin (i.e. Pin 24) which provides a temperature stable 3V output generated from the internal bandgap voltage and the **THRES** pin. If the RSSI level generated by the Limiter is higher than U_{thres} , the OTA generates a positive current I_{load} . This yields a voltage rise on the **TAGC** pin (Pin 4). Otherwise, the OTA generates a negative current. These currents do not have the same values in order to achieve a fast-attack and slow-release action of the AGC and are used to charge an external capacitor which finally generates the LNA gain control voltage.

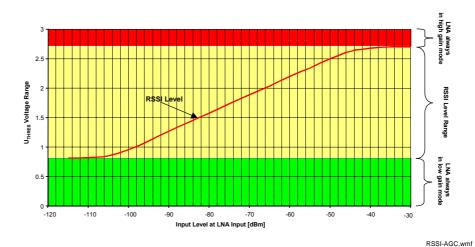


Figure 4-2 RSSI Level and Permissive AGC Threshold Levels

The switching point should be chosen according to the intended operating scenario. The determination of the optimum point is described in the accompanying Application Note, a threshold voltage level of 1.8V is apparently a viable choice. It should be noted that the output of the **3VOUT** pin is capable of driving up to 50µA, but that the **THRES** pin input current is only in the region of 40nA. As the current drawn out of the **3VOUT** pin is directly related to the receiver power consumption, the power divider resistors should have high impedance values. The sum of R1 and R2 has to be $600k\Omega$ in order to yield 3V at the **3VOUT** pin. R1 can thus be chosen as $240k\Omega$, R2 as $360k\Omega$ to yield an overall **3VOUT** output current of 5μ A¹ and a threshold voltage of 1.8V

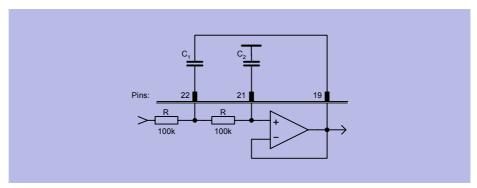
Note: If the LNA gain shall be kept in either high or low gain mode this has to be accomplished by tying the **THRES** pin to a fixed voltage. In order to achieve high gain mode operation, a voltage higher than 2.8V shall be applied to the **THRES** pin, such as a short to the **3VOLT** pin. In order to achieve low gain mode operation a voltage lower than 0.7V shall be applied to the **THRES**, such as a short to ground.

As stated above the capacitor connected to the **TAGC** pin is generating the gain control voltage of the LNA due to the charging and discharging currents of the OTA and thus is also responsible for the AGC time constant. As the charging and discharging currents are not equal two different time constants will result. The time constant corresponding to the charging process of the capacitor shall be chosen according to the data rate. According to measurements performed at Infineon the capacitor value should be greater than 47nF.

1. note the $20k\Omega$ resistor in series with the 3.1V internal voltage source

4.2 Data Filter Design

Utilising the on-board voltage follower and the two $100k\Omega$ on-chip resistors a 2nd order Sallen-Key low pass data filter can be constructed by adding 2 external capacitors between pins 19 (SLP) and 22 (FFB) and to pin 21 (OPP) as depicted in the following figure and described in the following formulas¹.



Filter Design.wmf

Figure 4-3 Data Filter Design

$$C1 = \frac{2Q\sqrt{b}}{R2\Pi f_{3dB}} \qquad C2 = \frac{\sqrt{b}}{4QR\Pi f_{3dB}}$$

with

$$Q = \frac{\sqrt{b}}{a}$$

(3) the quality factor of the poles

where

in case of a Bessel filter a = 1.3617, b = 0.618

and thus Q = 0.577

and in case of a Butterworth filter a = 1.141, b = 1

and thus Q = 0.71

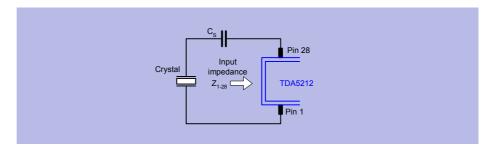
Example: Butterworth filter with $f_{3dB} = 5kHz$ and $R = 100k\Omega$:

$$C_1 = 450pF, C_2 = 225pF$$

1. taken from Tietze/Schenk: Halbleiterschaltungstechnik, Springer Berlin, 1999

4.3 Crystal Load Capacitance Calculation

The value of the capacitor necessary to achieve that the crystal oscillator is operating at the intended frequency is determined by the reactive part of the negative resistance of the oscillator circuit as shown in Section 5.1.3 and by the crystal specifications given by the crystal manufacturer.



Quartz load 5212.wmf

Figure 4-4 Determination of Series Capacitance Value for the Crystal Oscillator

Crystal specified with load capacitance

$$C_S = \frac{1}{\frac{1}{C_I} + 2\pi f X_L}$$

with C₁ the load capacitance (refer to the crystal specification).

Examples:

7.2 MHz: C_L = 12 pF X_L =500 Ω C_S = 9.5 pF 14.5 MHz: C_L = 12 pF X_L =1050 Ω C_S = 5.6 pF

These values may be obtained in high accuracy by putting two capacitors in series to the quartz, such as 18pF and 20pF in the 7.2MHz case and 18pF and 8.2pF in the 14.5MHz case.



4.4 Crystal Frequency Calculation

The local oscillator (UHF PLL) signal has to be high-side injected into the down-converting mixer. Thus the crystal frequency is calculated by using the following formula:

$$f_{QU} = (f_{RF} + 10.7) / r$$

with $f_{\rm RF}$ receive frequency

 f_{LO} local oscillator (PLL) frequency (f_{RF} + 10.7)

f_{OU} crystal oscillator frequency

r ratio of local oscillator (PLL) frequency and crystal

frequency as shown in the subsequent table.

Table 4-1 PLL Division Ratio Dependence on States of CSEL	
CSEL	Ratio r = (f _{LO} /f _{QU})
open	128
GND	64

This yields the following example:

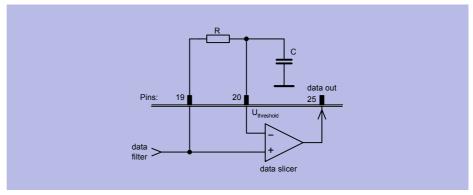
CSEL tied to GND:

$$f_{\text{QU}} = (915MHz + 10.7MHz)/64 = 14.4641 MHz$$



4.5 Data Slicer Threshold Generation

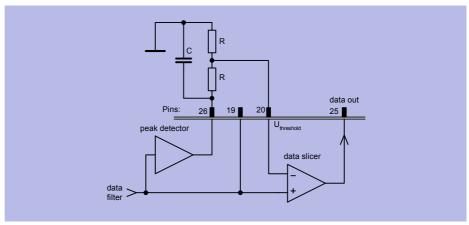
The threshold of the data slicer can be generated in two ways, depending on the signal coding scheme used. In case of a signal coding scheme without DC content such as Manchester coding the threshold can be generated using an external R-C integrator as shown in the following . The cut-off frequency of the R-C integrator has to be lower than the lowest frequency appearing in the data signal. In order to keep distortion low, the minimum value for R is $20k\Omega$.



Data_slice1.wmf

Figure 4-5 Data Slicer Threshold Generation with External R-C Integrator

Another possibility for threshold generation is to use the peak detector in connection with two resistors and one capacitor as shown in the following figure. The component values are depending on the coding scheme and the protocol used.



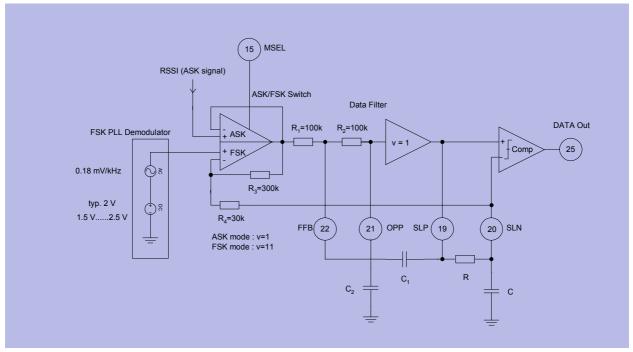
Data slice2.wm

Figure 4-6 Data Slicer Threshold Generation Utilising the Peak Detector



4.6 ASK/FSK Switch Functional Description

The TDA5211 is containing an ASK/FSK switch which can be controlled via Pin 15 (MSEL). This switch is actually consisting of 2 operational amplifiers that are having a gain of 1 in case of the ASK amplifier and a gain of 11 in case of the FSK amplifier in order to achieve an appropriate demodulation gain characteristic. In order to compensate for the DC-offset generated especially in case of the FSK PLL demodulator there is a feedback connection between the threshold voltage of the bit slicer comparator (Pin 20) to the negative input of the FSK switch amplifier. This is shown in the figure below:



ask_fsk_datapath.WMF

Figure 4-7 ASK/FSK mode datapath

4.6.1 FSK Mode

The FSK datapath has a bandpass characterisite due to the feedback shown above (highpass) and the data filter (lowpass). The lower cutoff frequency f2 is determined by the external RC-combination. The upper cutoff frequency f3 is determined by the data filter bandwidth.

The demodulation gain of the FSK PLL demodulator is $180\mu V/kHz$. This gain is increased by the gain v of the FSK switch, which is 11. Therefore the resulting dynamic gain of this circuit is 2mV/kHz within the bandpass. The gain for the DC

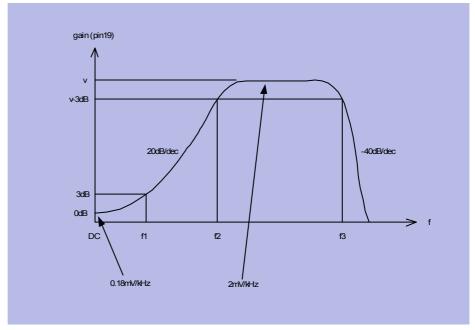


content of FSK signal remains at $180\mu\text{V/kHz}$. The cutoff frequencies of the bandpass have to be chosen such that the spectrum of the data signal is influenced in an acceptable amount.

In case that the user data is containing long sequences of logical zeros the effect of the drift-off of the bit slicer threshold voltage can be lowered if the offset voltage inherent at the negative input of the slicer comparator (Pin20) is used. The comparator has no hysteresis built in.

This offset voltage is generated by the bias current of the negative input of the comparator (i.e. 20nA) running over the external resistor R. This voltage raises the voltage appearing at pin 20 (e.g. 1mV with R = $100k\Omega$). In order to obtain benefit of this asymmetrical offset for the demodulation of long zeros the lower of the two FSK frequencies should be chosen in the transmitter as the zero-symbol frequency.

In the following figure the shape of the above mentioned bandpass is shown.



frequenzgang.WMF

Figure 4-8 Frequency characterstic in case of FSK mode

The cutoff frequencies are calculated with the following formulas:

$$f_1 = \frac{1}{2\pi \frac{R \cdot 330k\Omega}{R + 330k\Omega} \cdot C}$$

$$f_2 = v \cdot f_1 = 11 \cdot f_1$$

$$f_3 = f_{3dB}$$

 f_3 is the 3dB cutoff frequency of the data filter - see Section 4.2.

Example:

 $R = 100k\Omega$

C = 47nF

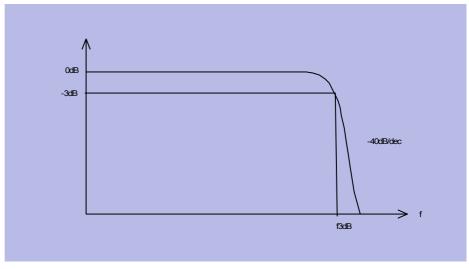
This leads to $f_1 = 44Hz$

and

 $f_2 = 485Hz$

4.6.2 ASK Mode

In case the receiver is operated in ASK mode the datapath frequency charactersitic is dominated by the data filter alone, thus it is lowpass shaped. The cutoff frequency is determined by the external capacitors C12 and C14 and the internal 100k resistors as described in Section 4.2



freq_ask.WMF

Figure 4-9 Frequency charcteristic in case of ASK mode



Principle of the Precharge Circuit

In case the data slicer threshold shall be generated with an external RC network as described in Section 4.5 it is necessary to use large values for the capacitor C attached to the SLN pin (pin 20) in order to achieve long time constants. This results also from the fact that the choice of the value for R connected between the **SLP** and **SLN** pins (pins 19 and 20) is limited by the $330k\Omega$ resistor appearing in parallel to R as can be seen in Figure 4-6. Apart from this a resistor value of $100k\Omega$ leads to a voltage offset of 1mv at the comparator input as described in Section 4.6.1. The resulting startup time constant τ_1 can be calculated with:

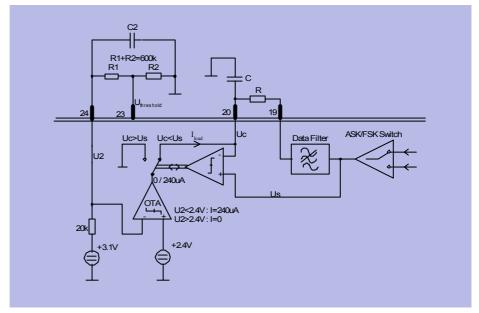
$$\tau_1 = (R // 330k\Omega) \cdot C$$

In case R is chosen to be $100k\Omega$ and C is chosen as 47nF this leads to

$$\tau_1 = (100 k\Omega // 330 k\Omega) \cdot 47 nF = 77 k\Omega \cdot 47 nF = 3.6 ms$$

When the device is turned on this time constant dominates the time necessary for the device to be able to demodulate data properly. In the powerdown mode the capacitor is only discharged by leakage currents.

In order to reduce the turn-on time in the presence of large values of C a precharge circuit was included in the TDA5210 as shown in the following figure.



precharge.WMF

Figure 4-10 Principle of the precharge circuit

This circuit charges the capacitor C with an inrush current I_{load} of 240µA for a duration of T_2 until the voltage U_c appearing on the capacitor is equal to the voltage U_s at the input of the data filter. This voltage is limited to 2.5V. As soon as these voltages are equal or the duration T_2 is exceeded the precharge circuit is disabled.

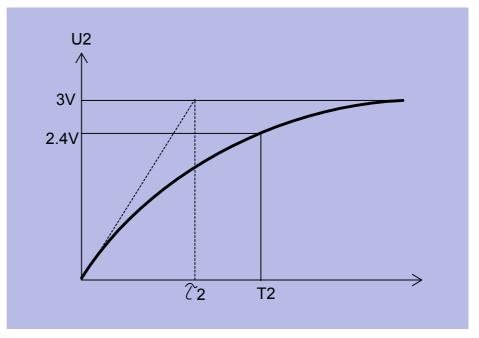
 τ_2 is the time constant of the charging process of C which can be calculated as

$$\tau_2 \approx 20 k\Omega \cdot C2$$

as the sum of R1 and R2 is sufficiently large and thus can be neglected. T2 can then be calculated according to the following formula:

$$T_2 = \tau_2 \ln \left(\frac{1}{1 - \frac{2.4V}{3V}} \right) \approx \tau_2 \cdot 1.6$$

The voltage transient during the charging of C2 is shown in the following figure:



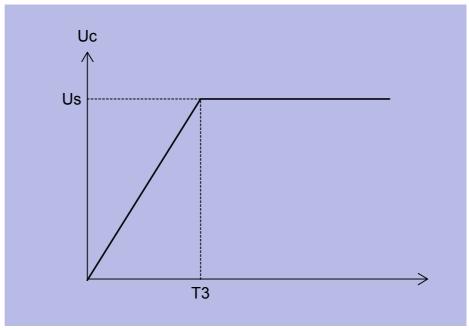
e-fkt1.WMF

Figure 4-11 Voltage appearing on C2 during precharging process

The voltage appearing on the capacitor C connected to pin 20 is shown in the following figure. It can be seen that due to the fact that it is charged by a constant current source it exhibits is a linear increase in voltage which is limited to

 U_{Smax} = 2.5V which is also the approximate operating point of the data filter input. The time constant appearing in this case can be denoted as T3, which can be calculated with

$$T3 = \frac{U_{\text{Smax}} \cdot C}{240 \mu A} = \frac{2,5 \text{V}}{240 \mu A} \cdot C$$



e-Fkt2.WMF

Figure 4-12 Voltage transient on capacitor C attached to pin 20

As an example the choice of C2 = 20nF and C = 47nF yields

 $\tau_2 = 0.4 \text{ms}$

 $T_2 = 0.64 ms$

 $T_3 = 0.49 ms$

This means that in this case the inrush current could flow for a duration of 0.64ms but stops already after 0.49ms when the U_{Smax} limit has been reached. T3 should always be chosen to be shorter than T2.

It has to be noted finally that during the turn-on duration T2 the overall device power consumption is increased by the 240µA needed to charge C.



The precharge circuit may be disabled if C2 is not equipped. This yields a T2 close to zero. Note that the sum of R4 and R5 has to be $600k\Omega$ in order to produce 3V at the THRES pin as this voltage is internally used also as the reference for the FSK demodulator.

5.4

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5.1 Electrical Data

5.1.1 Absolute Maximum Ratings



WARNING

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC will result.

Tabl	Table 5-1 Absolute Maximum Ratings, Ambient temperature T _{AMB} =-40°C + 85°C								
#	Parameter	Symbol	Limit \	Limit Values		Remarks			
			min	max					
1	Supply Voltage	V _s	-0.3	5.5	V				
2	Junction Temperature	Tj	-40	+150	°C				
3	Storage Temperature	T _s	-40	+125	°C				
4	Thermal Resistance	R _{thJA}		114	K/W				
5	ESD integrity, all pins	V _{ESD}	-1	+1	kV	HBM according to MIL STD 883D, method 3015.7			

5.1.2 Operating Range

Within the operating range the IC operates as explained in the circuit description. The AC/DC characteristic limits are not guaranteed.

Supply voltage: VCC = 4.5V .. 5.5V

Tab	Table 5-2 Operating Range, Ambient temperature T _{AMB} = -40°C + 85°C									
#	Parameter	Symbol	Limit '	Values	Unit	Test Conditions	L	Item		
			min	max						
1	Supply Current	I _{SF} I _{SA}		6 5.4	mA mA	f_{RF} = 915MHz, FSK Mode f_{RF} = 915MHz, ASK Mode				
2	Receiver Input Level ASK FSK, frequ. dev. ± 50kHz	RF _{in}	-109 -102	-13 -13	dBm dBm	$@$ source impedance 50Ω , BER 2E-3, average power level, Manchester encoded datarate 4kBit, 280kHz IF Bandwidth				
3	LNI Input Frequency	f _{RF}	910	920	MHz					
4	MI/X Input Frequency	f _{MI}	910	920	MHz					
6	UHF Local Oscillator Frequency Range	f _{LO}	920	930	MHz					
7	3dB IF Frequency Range	f _{IF -3dB}	5	23	MHz					
8	Powerdown Mode On	PWDN _{ON}	0	0.8	V					
9	Powerdown Mode Off	PWDN _{OFF}	2	VS	V					
10	Gain Control Voltage, LNA high gain state	V _{THRES}	2.8	V _S	V					
11	Gain Control Voltage, LNA low gain state	V _{THRES}	0	0.7V	V					

This value is guaranteed by design.



5.1.3 AC/DC Characteristics

AC/DC characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production. The device performance parameters marked with were measured on an Infineon evaluation board as desdribed in Section 5.2

Tak	ole 5-3 AC/DC Characterist	ics with T _A 2	25 °C, V _V	CC = 4.5 .	5.5 V							
#	Parameter	Symbol	L	imit Valu	ies	Unit	Test Conditions	L	Item			
			min	typ	max							
Su	Supply											
Su	oply Current											
1	Supply current, standby mode	I _{S PDWN}		90	120	nA	Pin 27 (PDWN) open or tied to 0 V					
2	Supply current, device operating in FSK mode	I _{SF}		5.4	5.7	mA	Pin 11 (FSEL) open, Pin 15 (MSEL) tied to GND					
3	Supply current, device operating in ASK mode	I _{SA}		4.8	5.1	mA	Pin 11 (FSEL) open, Pin 15 (MSEL) open					
LNA Signal Input LNI (PIN 3), V _{THRES} > 2.8V, high gain mode												
			gn gain i									
1	Average Power Level at BER = 2E-3 (Sensitivity) ASK	RF _{in}		-112		dBm	Manchester encoded datarate 4kBit, 280kHz IF Bandwidth					
2	Average Power Level at BER = 2E-3 (Sensitivity) FSK	RF _{in}		-105		dBm	Manchester enc. datarate 4kBit, 280kHz IF Bandw., ± 50kHz pk. dev.					
3	Input impedance, f _{RF} = 915 MHz	S _{11 LNA}	0.7	17 / -78.4	deg							
4	Input level @ 1dB C.P. f _{RF} =915 MHz	P1dB _{LNA}		t.b.d.		dBm						
5	Input 3 rd order intercept point f _{RF} = 915 MHz	IIP3 _{LNA}		t.b.d.		dBm	f _{in} = 914 & 916MHz					
6	LO signal feedthrough at antenna port	LO _{LNI}			t.b.d.	dBm						
Sig	nal Output LNO (PIN 6), V _{TI}	HRES > 2.8V,	high gai	n mode								
1	Gain f _{RF} = 915 MHz	S _{21 LNA}	1.4	101 / 98.4	deg							
2	Output impedance, f _{RF} = 915 MHz	S _{22 LNA} 0.869 / -25.7 deg										



#	ole 5-3 AC/DC Characterist Parameter	Symbol		imit Valu		Unit	Test Conditions	L	Item
π	i di dilletei	Gymbol	min	typ	max	Oille	rest conditions	-	item
3	Voltage Gain Antenna to MI f _{RF} = 915 MHz	G _{AntMI}		t.b.d.		dB			
4	Noise Figure	NF _{LNA}		t.b.d.		dB			
Sig	Signal Input LNI, V _{THRES} = GND, low gain mode								
1	Input impedance, f _{RF} = 915 MHz	nce, S _{11 LNA} 0.753 / -86.26 deg							
2	Input level @ 1dB C. P. f _{RF} = 915 MHz	P1dB _{LNA}		t.b.d.		dBm			
Sig	nal Input LNI, V _{THRES} = GN	ID, low gain	mode						
3	Input 3 rd order intercept point f _{RF} = 915 MHz	IIP3 _{LNA}		t.b.d.		dBm	f _{in} = 914 & 916MHz		
Sig	nal Output LNO, V _{THRES} =	GND, low ga	in mode						
1	Gain f _{RF} = 915 MHz	S _{21 LNA}	0.1	74 / 107.4	l deg				
2	Output impedance, f _{RF} = 915 MHz	S _{22 LNA}	0.8	668 / -28.1	deg				
3	Voltage Gain Antenna to MI f _{RF} = 915 MHz	G _{AntMI}		t.b.d.		dB			
Sig	nal 3VOUT (PIN 24)								
1	Output voltage	V _{3VOUT}	2.9	3	3.1	V	$I_{3Vout} = 5\mu A$		
2	Current out	I _{3VOUT}			50	μA			
Sig	nal THRES (PIN 23)								
1	Input Voltage range	V _{THRES}	0		V _S -1V	V	see Section 4.1		
2	LNA low gain mode	V _{THRES}	0			V			
3	LNA high gain mode	V _{THRES}	2.8	3	V_S	V	or shorted to Pin 24		
4	Current in	I _{THRES_in}		5		nA			
Sig	nal TAGC (PIN 4)								
1	Current out, LNA low gain state	I _{TAGC_out}	3.8	4.2	4.8	μA	RSSI > V _{THRES}		
2	Current in, LNA high gain state	I _{TAGC_in}	1	1.5	2	μA	RSSI < V _{THRES}		
MIXER									
Sig	nal Input MI/MIX (PINS 8/9)								
1	Input impedance, f _{RF} = 915 MHz	S _{11 MIX}	0.9	12 / -30.1	3 deg				
2	Input 3 rd order intercept point	IIP3 _{MIX}		-25		dBm			



	Parameter	Symbol	L	imit Valu	ies	Unit	Test Conditions	L	Item
			min	typ	max				
Sig	nal Output IFO (PIN 12)								
1	Output impedance	Z _{IFO}		330		Ω			
2	Conversion Voltage Gain f _{RF} =869 MHz	G _{MIX}		t.b.d.		dB			
3	Noise Figure, SSB (~DSB NF+3dB)	NF _{MIX}		t.b.d.		dB			
4	RF to IF isolation	A _{RF-IF}		t.b.d.		dB			
	IITER nal Input LIM/X (PINS 17/18)							
1	Input Impedance	, Z _{LIM}	264	330	396	Ω			
2	RSSI dynamic range	DR _{RSSI}	60		80	dB			
3	RSSI linearity	LIN _{RSSI}		±1		dB			
4	Operating frequency (3dB points)	f _{LIM}	5	10.7	23	MHz			
1	TA FILTER Useable bandwidth	BW _{BB} FILT			100	kHz			
SLI	CER								
	nal Output DATA (PIN 25)								
1	Useable bandwith	BW _{BB} SLIC			100	kHz			
2	Capacitive loading of output	C _{max} SLIC			20	pF			
3	LOW output voltage	V _{SLIC_L}		0	0.1	V			
4	HIGH output voltage	V _{SLIC_H}	V _S -1.1V	V _S -1V	V _S -0.9V	V			
5	Output current	I _{SLIC_out}	600	750	900	μA			
6	Leakage current	I _{SLIC_in}	30	33	36	μA			
PE.	AK DETECTOR								
Sig	nal Output PDO (PIN 26)								
1	LOW output voltage	V _{SLIC_L}		0	0.1	V			
2	HIGH output voltage	V _{SLIC_H}	2.9	3	3.1	V			
3	Load current	I _{load}	700	850	1000	μΑ			
4	Leakage current	I _{leakage}	580	700	820	nA			



	Parameter	Symbol	L	imit Valu	ies	Unit	Test Conditions	L	Item
		-	min	typ	max				
CR	YSTAL OSCILLATOR								
	nals CRSTL1, CRISTL 2, (Pl	NS 1/28)							
1	Operating frequency	fCRSTL	6		15	MHz	fundamental mode, series resonance		
2	Input Impedance @ ~7.2MHz	Z ₁₋₂₈		- 860 + j500		Ω			
3	Input Impedance @ ~14.5MHz	Z ₁₋₂₈		- 550 + j1050		Ω			
4	Serial Capacity @ ~7.2MHz	C _{S7} =C1		9.5		pF			
5	Serial Capacity @ ~14.5MHz	C _{S14} =C1		5.6		pF			
AS	K/FSK Signal Switch								
Sig	nal MSEL (PIN 15)								
1	FSK Mode	V_{MSEL}	1.4		4	V	or open		
2	ASK Mode	V_{MSEL}	0		0.2	V			
FSI	K DEMODULATOR								
1	Demodulation Gain	G _{FMDEM}	180	200	220	μV/ kHz			
2	Useable IF Bandwidth	BW _{IFPLL}	10.2	10.7	11.2	MHz			
PO	WER DOWN MODE								
Sig	nal PDWN (PIN 27)								
1	Powerdown Mode On	PWDN _{ON}	0		0.8	V			
2	Powerdown Mode Off	PWDN _{Off}	2.8		V _S	V			
3	Input bias current PDWN	I _{PDWN}		t.b.d.		μΑ			
4	Start-up Time until valid IF signal is detected	T _{SU}			1	ms	note: startup - time is also dependent on data filter and data slicer time constants		
PLL DIVIDER									
Sig	nal CSEL (PIN 16)								
1	f _{CRSTL} range 7.xxMHz	V_{CSEL}	1.4		4	V	or open		



Tak	Table 5-3 AC/DC Characteristics with T _A 25 °C, V _{VCC} = 4.5 5.5 V (continued)										
	Parameter	Symbol	Limit Values			Unit	Test Conditions	L	Item		
			min	typ	max						
2	f _{CRSTL} range 14.xxMHz	V _{CSEL}	0		0.2	V					
3	Input bias current CSEL	I _{CSEL}		5		μA	CSEL tied to GND				

Measured only in lab.



5.2 Test Circuit

The device performance parameters marked with in Section 5.1.3 were measured on an Infineon evaluation board.

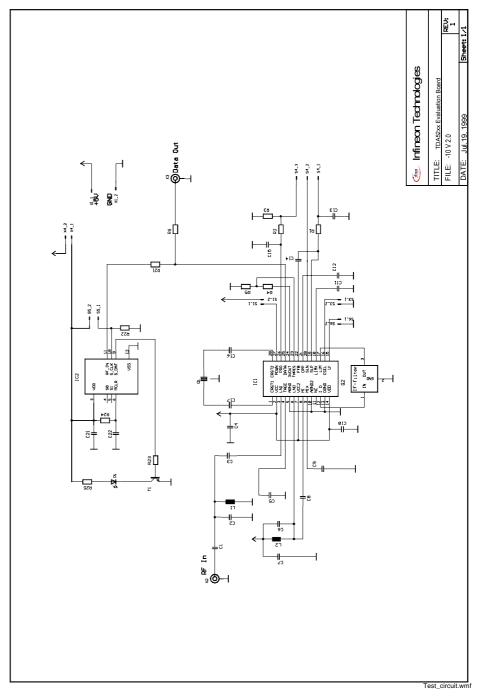


Figure 5-1 Schematic of the Evaluation Board

Wireless Components 5 - 9 Specification, May 2003



5.3 Test Board Layouts

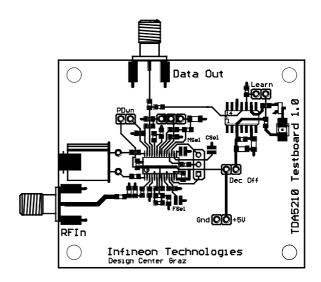


Figure 5-2 Top Side of the Evaluation Board

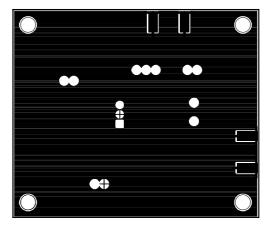


Figure 5-3 Bottom Side of the Evaluation Board



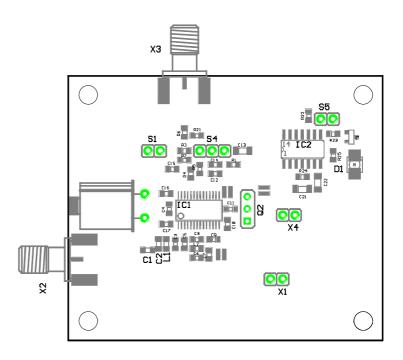


Figure 5-4 Component Placement on the Evaluation Board



5.4 Bill of Materials

The following components are necessary for evaluation of the TDA5212 at 915 MHz without use of a Microchip HCS515 decoder.

Table 5-4 Bill of	of Materials	
Ref	Value	Specification
R1	100kΩ	0805, ± 5%
R2	100kΩ	0805, ± 5%
R3	820kΩ	0805, ± 5%
R4	240kΩ	0805, ± 5%
R5	360kΩ	0805, ± 5%
R6	10kΩ	0805, ± 5%
L1	3.3nH	Toko, PTL2012-F15N0G
L2	3.9nH	0805,COG, ± 2%
C1	1pF	0805, COG, ± 0.1pF
C2	3.3pF	0805, COG, ± 0.1pF
C3	4.7pF	0805, COG, ± 0.1pF
C4	100pF	0805, COG, ± 5%
C5	47nF	1206, X7R, ± 10%
C6	3.3pF	Toko, PTL2012-F15N0G
C7	100pF	0805, COG, ± 5%
C8	22pF	0805, COG, ± 5%
C9	100pF	0805, COG, ± 5%
C10	10nF	0805, X7R, ± 10%
C11	10nF	0805, X7R, ± 10%
C12	220pF	0805, COG, ± 5%
C13	47nF	0805, X7R, ± 10%
C14	470pF	0805, COG, ± 5%
C15	47nF	0805, X7R, ± 10%
C16	8.2pF	0805, COG, ± 1%
C17	18pF	0805, COG, ± 0.25pF
Q1	14.129690MHz	Jauch Q 14.129690-S1
Q2	SFE10.7MA5-A	Murata
X2, X3	142-0701-801	Johnson
X1, X4, S1, S5	STL_2POL	2-pole pin connector
S4	STL_3POL	3-pole pin connector, or not equipped
IC1	TDA 5212	Infineon



The following components are necessary in addition to the above mentioned ones for evaluation of the TDA5212 in conjunction with a Microchip HCS515 decoder.

Table 5-5 Bill of	of Materials Addendum	
Ref	Value	Specification
R21	22 kΩ	0805, ± 5%
R22	10kΩ	0805, ± 5%
R23	22 kΩ	0805, ± 5%
R24	820kΩ	0805, ± 5%
R25	560kΩ	0805, ± 5%
C21	100nF	1206, X7R, ± 10%
C22	100nF	1206, X7R, ± 10%
IC2	HCS512	Microchip
T1	BC 847B	Infineon
D1	LS T670-JL	Infineon